

isc N-Channel MOSFET Transistor

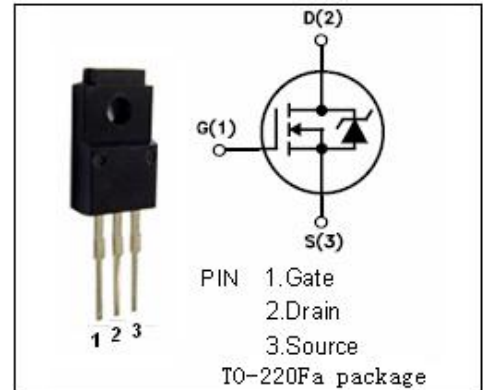
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DESCRIPTION

- Drain Current $-I_D=4A @ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}=600V(\text{Min})$

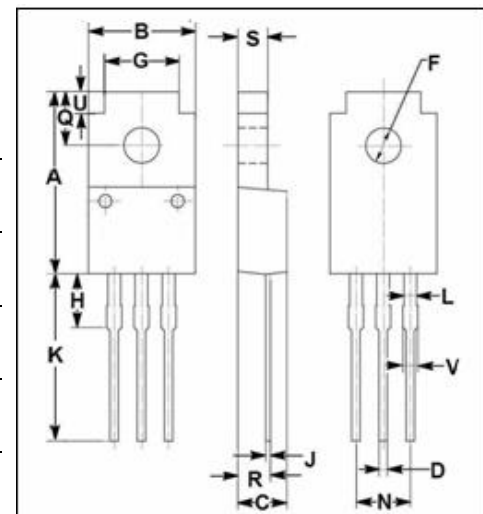
APPLICATIONS

- Designed for high voltage, high speed power switching



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	600	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_C=25^\circ C$	4	A
P_{tot}	Total Dissipation@ $T_C=25^\circ C$	50	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



DIM	mm	
	MIN	MAX
A	16.85	17.15
B	9.90	10.10
C	4.35	4.65
D	0.75	0.80
F	3.20	3.40
G	6.90	7.10
H	5.15	5.45
J	0.45	0.75
K	13.35	13.65
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.95	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	0.83	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	35	$^\circ C/W$

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• ELECTRICAL CHARACTERISTICS (T_C=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	600			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =25 V _{GS} ; I _D =1mA	1.0		5.0	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D = 2A		1.2	1.8	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0			±1	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =480V; V _{GS} = 0			0.1	mA
ton	Turn-on time	V _{GS} =10V; I _D =2A; R _L =75 Ω		40		ns
toff	Turn-off time			360		ns